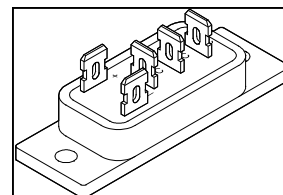


TECHNICAL DATA
DATA SHEET 1175, REV -**THREE PHASE FULL WAVE
BRIDGE RECTIFIER ASSEMBLY**

DESCRIPTION: A 200/400/600 VOLT, 18 AMP, 70 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAXIMUM RATINGSAll ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S25A320S7 S25A340S7 S25A360S7	-	-	-	200 400 600	Vdc
Average DC Output Current ($T_C = \text{Case Temp}$) (I_o)	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	-	18 13.5 9.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	4.5 3.6 2.3	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Thermal Resistance (θ_{JL})	-	-	-	1.5	$^\circ\text{C/W}$
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage (V_f)	$I_f = 9\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.75	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$	-	-	70	nsec

MECHANICAL DIMENSIONS: In Inches / mm

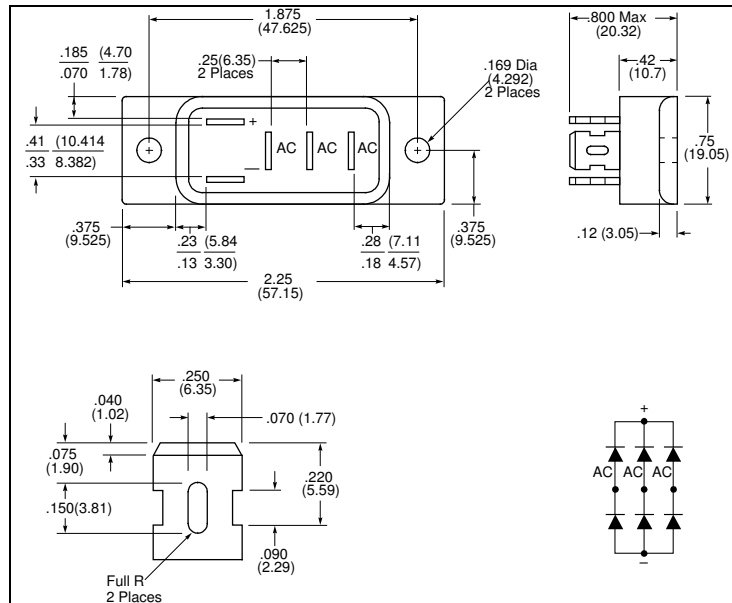


FIG. 404

Note: Case finish - Black Anodized

TECHNICAL DATA

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